Agilent Technologies
Innovating the HP Way

Cascadable Silicon Bipolar MMIC Amplifier

Technical Data

MSA-0711

Features

- **Cascadable 50 Ω Gain Block**
- **3 dB Bandwidth:** DC to 1.9 GHz
- **12.0 dB Typical Gain at 1.0 GHz**
- **Unconditionally Stable (k>1)**
- **Low Cost Surface Mount Plastic Package**
- **Tape-and-Reel Packaging Option Available[1]**

Note:

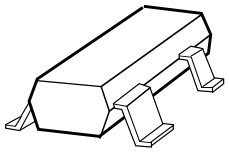
1. Refer to PACKAGING section "Tape-and-Reel Packaging for Surface Mount Semiconductors".

Description

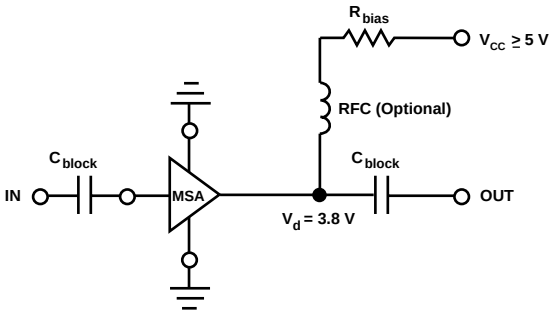
The MSA-0711 is a low cost silicon bipolar Monolithic Microwave Integrated Circuit (MMIC) housed in the surface mount plastic SOT-143 package. This MMIC is designed for use as a general purpose 50 Ω gain block. Typical applications include narrow and broad band IF and RF amplifiers in commercial and industrial applications.

The MSA-series is fabricated using Agilent's 10 GHz f_T, 25 GHz f_{MAX}, silicon bipolar MMIC process which uses nitride self-alignment, ion implantation, and gold metallization to achieve excellent performance, uniformity and reliability. The use of an external bias resistor for temperature and current stability also allows bias flexibility.

SOT-143 Package



Typical Biasing Configuration



MSA-0711 Absolute Maximum Ratings

Parameter	Absolute Maximum[1]
Device Current	50 mA
Power Dissipation[2,3]	175 mW
RF Input Power	+13 dBm
Junction Temperature	150°C
Storage Temperature	–65 to 150°C

Thermal Resistance[2,4]:
θ_{jc} = 505°C/W

Notes:
1. Permanent damage may occur if any of these limits are exceeded.
2. T_{CASE} = 25°C.
3. Derate at 2.0 mW/°C for T_C > 62°C.
4. See MEASUREMENTS section "Thermal Resistance" for more information.

Electrical Specifications[1], T_A = 25°C

Symbol	Parameters and Test Conditions: I_d = 22 mA, Z_O = 50 Ω		Units	Min.	Typ.	Max.
G_P	Power Gain ($\|S_{21}\|^2$)	f = 0.1 GHz f = 1.0 GHz	dB	 10.0	13.0 12.0	
ΔG_P	Gain Flatness	f = 0.1 to 1.3 GHz	dB		±0.8	
$f_{3\ dB}$	3 dB Bandwidth		GHz		3.2	
VSWR	Input VSWR	f = 0.1 to 2.0 GHz			1.5:1	
	Output VSWR	f = 0.1 to 2.0 GHz			1.5:1	
NF	50 Ω Noise Figure	f = 1.0 GHz	dB		5.0	
$P_{1\ dB}$	Output Power at 1 dB Gain Compression	f = 1.0 GHz	dBm		5.5	
IP_3	Third Order Intercept Point	f = 1.0 GHz	dBm		18.0	
t_D	Group Delay	f = 1.0 GHz	psec		145	
V_d	Device Voltage	T_C = 25°C	V	3.0	3.8	4.6
dV/dT	Device Voltage Temperature Coefficient		mV/°C		–7.0	

Note:
1. The recommended operating current range for this device is 15 to 30 mA. Typical performance as a function of current is on the following page.

Part Number Ordering Information

Part Number	No. of Devices	Container
MSA-0711-TR1	3000	7" Reel
MSA-0711-BLK	100	Antistatic Bag

For more information, see "Tape and Reel Packaging for Semiconductor Devices".

MSA-0711 Typical Scattering Parameters (Z_O = 50 Ω, T_A = 25°C, I_d = 22 mA)

Freq. GHz	S_{11}		S_{21}			S_{12}			S_{22}	
	Mag	Ang	dB	Mag	Ang	dB	Mag	Ang	Mag	Ang
0.1	.03	1	13.0	4.47	174	–18.6	.118	1	.19	–8
0.2	.04	1	12.9	4.42	168	–18.5	.119	2	.19	–18
0.4	.04	–4	12.8	4.38	157	–18.4	.120	4	.19	–36
0.6	.05	–19	12.6	4.28	146	–18.1	.125	9	.19	–52
0.8	.07	–32	12.3	4.14	135	–17.7	.130	10	.20	–68
1.0	.08	–44	12.0	3.99	123	–17.4	.135	12	.19	–82
1.5	.13	–88	10.9	3.52	98	–16.1	.157	13	.19	–113
2.0	.18	–130	9.8	3.08	75	–15.2	.173	8	.18	–138
2.5	.25	–155	8.6	2.68	61	–14.7	.184	9	.18	–151
3.0	.32	–178	7.2	2.30	42	–14.7	.185	5	.17	–158
3.5	.38	165	5.8	1.96	26	–14.8	.181	3	.17	–150
4.0	.42	152	4.5	1.68	12	–14.7	.184	1	.20	–142

A model for this device is available in the DEVICE MODELS section.

Typical Performance, T_A = 25°C

(unless otherwise noted)

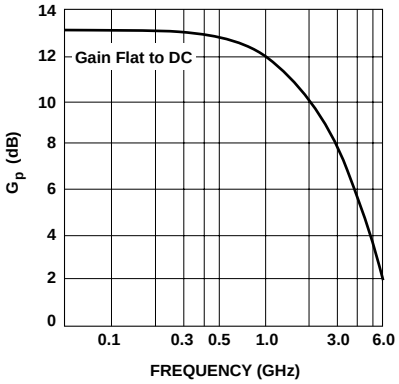


Figure 1. Power Gain vs. Frequency, I_d = 22 mA.

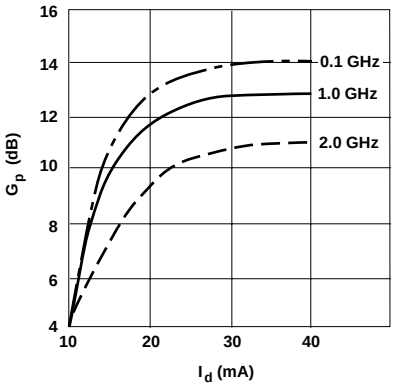


Figure 2. Power Gain vs. Current.

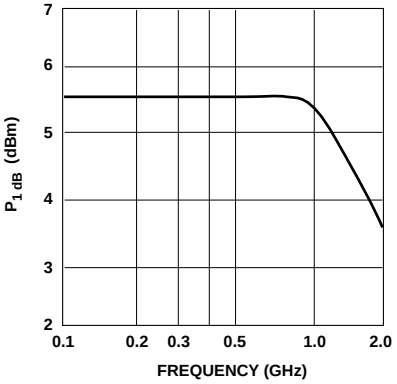


Figure 3. Output Power at 1 dB Gain Compression vs. Frequency, I_d = 22 mA.

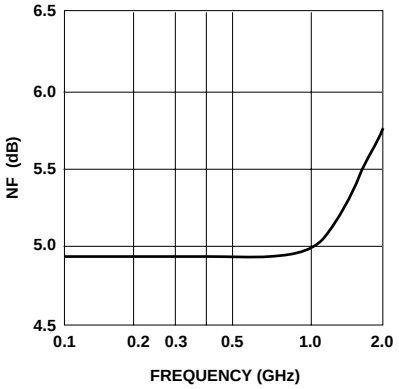


Figure 4. Noise Figure vs. Frequency, I_d = 22 mA.

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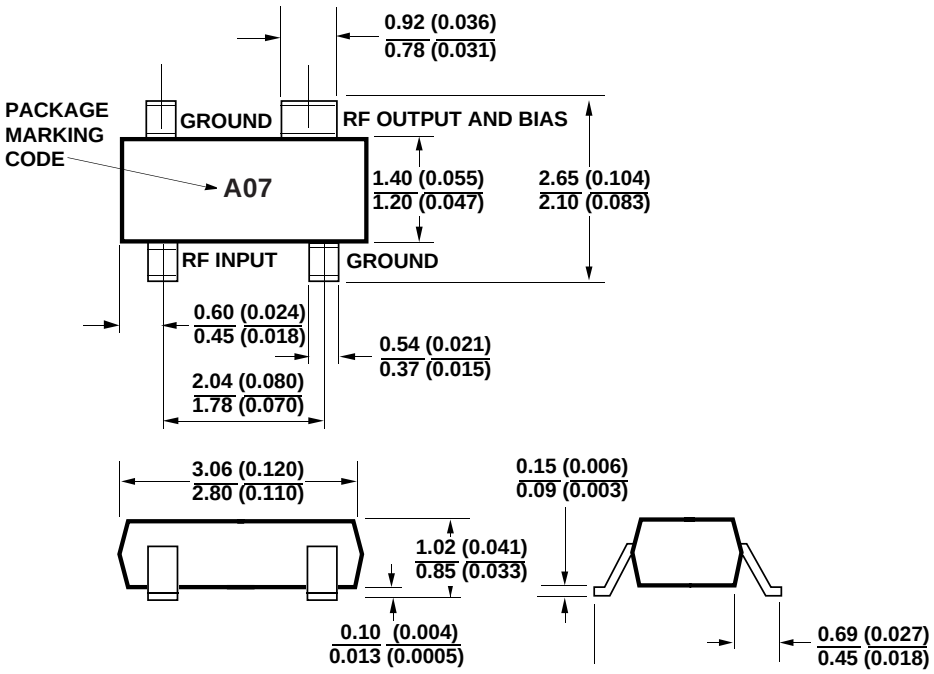
SOT-143 Package Dimensions



DIMENSIONS ARE IN MILLIMETERS (INCHES)

www.semiconductor.agilent.com
Data subject to change.

5965-9590E (11/99)